

P-Channel MOSFET

General Description

The WSK92P06 is the highest performance trench P-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSK92P06 meet the RoHS and Green Product requirement , 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

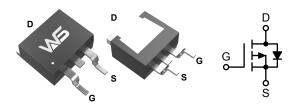
Product Summery

BV _{DSS}	R _{DSON}	I _D
-60V	10mΩ	-90A

Applications

- Power Management
- Load Switch

TO-263-2L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-60	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25℃	Continuous Drain Current, -V _{GS} @ -10V	-90	A
I _D @T _C =100℃	Continuous Drain Current, -V _{GS} @ -10V	-40	A
I _{DM}	Pulsed Drain Current	-190	А
P _D @T _C =25℃	Total Power Dissipation	96	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range -55 to 1		°C

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
R _{eja}	Thermal Resistance Junction-Ambient		62	°C/W
R _{θJC}	Thermal Resistance Junction-Case		1.3	°C/W



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Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-60			V	
Р	Static Drain-Source On-Resistance	V _{GS} =-10V , I _D =-18A		10	14	m 0	
R _{DS(ON)}	Static Drain-Source Off-Resistance	V _{GS} =-4.5V , I _D =-12A		13	18	18 mΩ	
V _{GS(th)}	Gate Threshold Voltage	V_{GS} = V_{DS} , I_D =-250 uA	-1.1	-1.8	-2.5	V	
I _{DSS}	Drain-Source Leakage Current	$V_{\text{DS}}\text{=-48V}$, $V_{\text{GS}}\text{=}0\text{V}$, $T_{\text{J}}\text{=}25^\circ\!\mathrm{C}$			1	uA	
I _{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$			±100	nA	
Qg	Total Gate Charge	VDS = -30 V, VGS = -10 V,		89			
Q _{gs}	Gate-Source Charge	$D_{S} = -30 \text{ V}, \text{ VGS} = -10 \text{ V},$		12		nC	
Q _{gd}	Gate-Drain Charge	ID=-17A		32			
T _{d(on)}	Turn-On Delay Time	Vdd = -30 V,		15			
Tr	Rise Time	$R_L = 30\Omega$, $I_D = -1 A$,		13			
T _{d(off)}	Turn-Off Delay Time	$V_{\text{GEN}} = -10 \text{ V}, \text{ Rg} = 6\Omega$		110		ns	
T _f	Fall Time			60			
C _{iss}	Input Capacitance			4066			
Coss	Output Capacitance	VDS=-30V,VGS=0V, f=1.0MHz		501		pF	
C _{rss}	Reverse Transfer Capacitance			291			

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current	T _C =25 [°] C			-40	А
V _{SD}	Diode Forward Voltage	V_{GS} =0V , I_{S} =-1A , T_{J} =25 $^{\circ}$ C			-1.2	V

A: The value of R e JA is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with TA=25C. The value in any given

application depends on the user's specific board design.

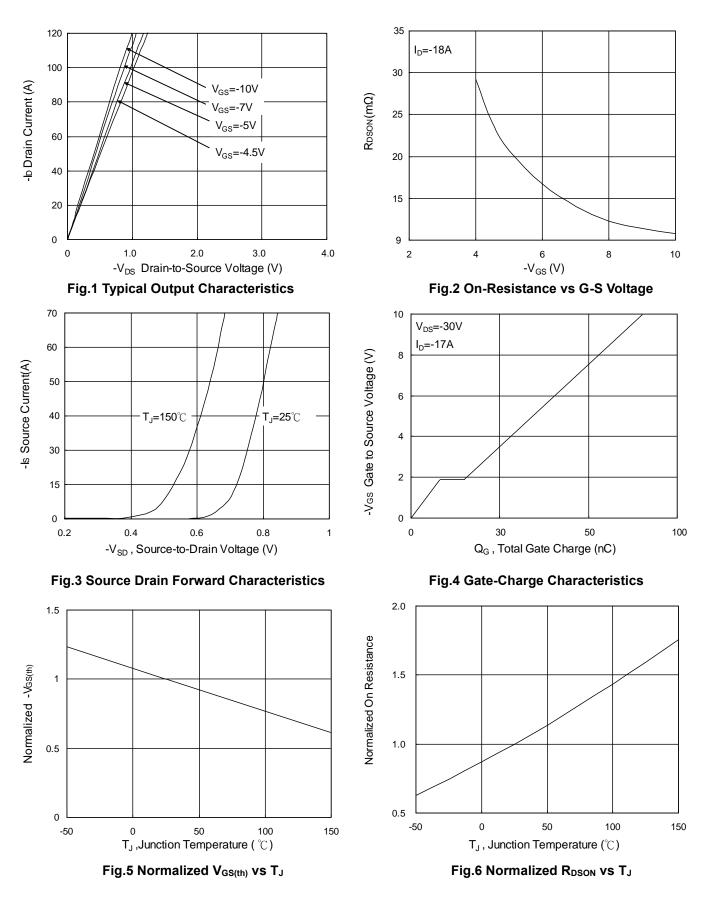
B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the t≤ 10s junction to ambient thermal resistance rating.



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Typical Characteristics





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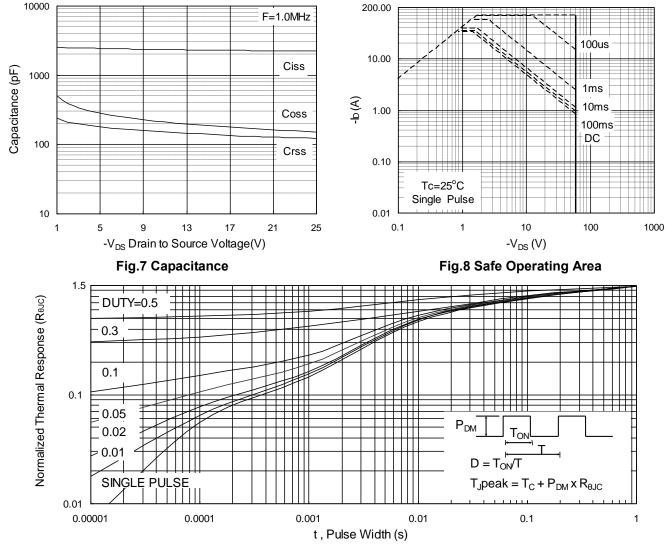
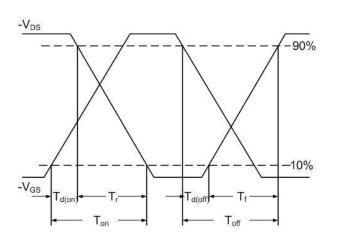
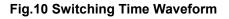


Fig.9 Normalized Maximum Transient Thermal Impedance





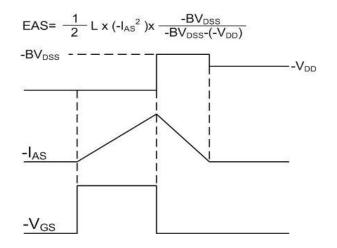
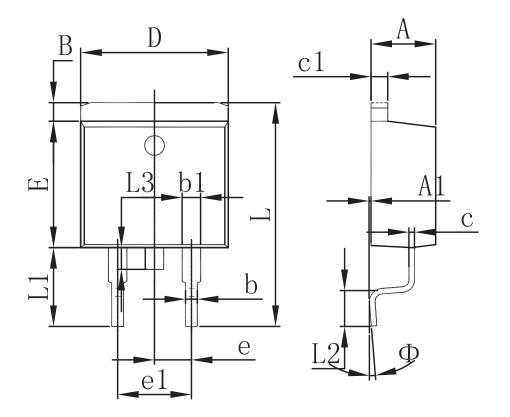


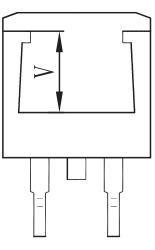
Fig.11 Unclamped Inductive Waveform



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Packaging information





Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	4.470	4.670	0.176	0.184	
A1	0.000	0.150	0.000	0.006	
В	1.120	1.420	0.044	0.056	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.310	0.530	0.012	0.021	
c1	1.170	1.370	0.046	0.054	
D	10.010	10.310	0.394	0.406	
E	8.500	8.900	0.335	0.350	
е	2.540	TYP.	0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
L	14.940	15.500	0.588	0.610	
L1	4.950	5.450	0.195	0.215	
L2	2.340	2.740	0.092	0.108	
L3	1.300	1.700	0.051	0.067	
Φ	0°	8°	0°	8°	
V	5.600	REF.	0.220REF.		



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